

SOT23 SILICON EPITAXIAL SCHOTTKY
BARRIER SINGLE AND DUAL DIODES

BAT54

ISSUE 3– JULY 95



PARTMARKING DETAILS

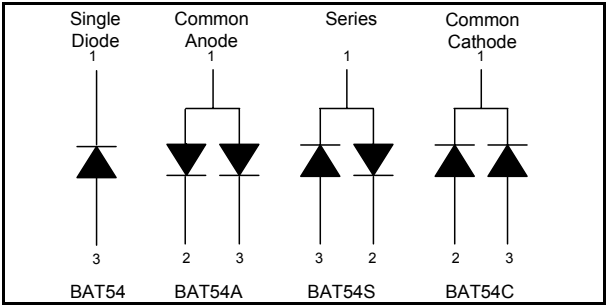
- Single Diode – L4Z
- Common Anode – L42
- Series – L43
- Common Cathode – L44

FEATURES

- Low V_F
- High current capability

APPLICATIONS

- P.S.U.
- Mobile telecomms. & SCSI



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Forward Voltage	V_F	400	mV
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{(BR)R}$	30			V	$I_R=10mA$
Forward Voltage	V_F		500	240 320 400 500 1000	mV mV mV mV mV	$I_F=0.1mA$ $I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$
Reverse Current	I_R			4	μA	$V_R=25V$
Diode Capacitance	C_D			10	pF	$f=1MHz, V_R=1V$
Reverse Recover Time	t_{rr}			5	ns	switched from $I_F=10mA$ to $I_R=10mA$ $R_L=100\Omega$, Measured at $I_R=1mA$